



PECVD SiO 6600 nm

Document Number:
Document Owner: ECTI
Approved by:
Created :
Revision #: 0
Revision date: April 11, 2008

Summary:

This document describes how to deposit a silicon oxide film of 6600 nm thickness on silicon wafer.

Table of content

1	Associated Documents & References	1
2	Equipment Used	1
3	Verifications Prior to Processing	2
4	Recipe description	2
5	Technical Data	2
6	Measurements & Statistical Process Control	2
6.1	Measurements	Fout! Bladwijzer niet gedefinieerd.
7	Record of Revisions	2

1 Associated Documents & References

MSDS if chemicals or gas involved.
pecvd Standard operating procedure
Rules and procedures of cleanroom

2 Equipment Used

Oxford Instrument (www.oxinst.com) "Plasmalab System 100 " plasma enhanced chemical vapor deposition (peCVD) system in Room 7175.

This equipment has to be reserved through the online resource scheduler. If you need training by the technician, check availability with him before reserving the equipment. Users have to go through regular training before using this equipment alone.



3 Verifications Prior to Processing

pecvd processing chamber has been gas plasma cleaned by previous user. Check with technician if the chamber needs to be opened for a physical clean scrubbing.

4 Recipe description

Start and warm up Oxford PECVD according to PECVD Standard Operating Procedure.

Set PECVD chuck temperature at 300 C.

Run Clean recipe CF4/O2 on empty chamber.

Load sample into chamber.

Pumpdown 3 minutes.

Preheat with N₂ gas, 600 mTorr, 1000 sccm, 5 min

Plasma clean with N₂ 1500 mTorr , 1000 sccm, 100 watts, 30 sec.

Deposit at 1500 mTorr with silane 5% in nitrogen 1000 sccm, N₂O at 1000 sccm
RF at 150 watt

Run time 20 minutes.

Pump out chamber for 1 minute.

Unload sample from chamber.

Wait for sample to cool before attempting to pick it up.

Resulting film is 6600 nm on silicon as measured with profilometer

5 Technical Data

6 Measurements & Statistical Process Control

7 Record of Revisions

Rev. 0

First Edition